Low Noise Transistor

NPN Silicon

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	60	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

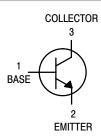
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1U = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

D	evice	Package	Shipping [†]
ММВ	T2484LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	60	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _(BR) CBO	60	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current $(V_{CB} = 45 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 45 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I _{CBO}	- -	10 10	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	10	nAdc
ON CHARACTERISTICS				•
DC Current Gain $ \begin{aligned} \text{(I}_{C} &= 1.0 \text{ mAdc, V}_{CE} = 5.0 \text{ Vdc)} \\ \text{(I}_{C} &= 10 \text{ mAdc, V}_{CE} = 5.0 \text{ Vdc)} \end{aligned} $	h _{FE}	250 -	_ 800	-
Collector – Emitter Saturation Voltage (I _C = 1.0 mAdc, I _B = 0.1 mAdc)	V _{CE(sat)}	-	0.35	Vdc
Base – Emitter On Voltage ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	V _{BE(on)}	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				•
Output Capacitance $(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{obo}	-	6.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C _{ibo}	-	6.0	pF
Noise Figure (I _C = 10 μ Adc, V _{CE} = 5.0 Vdc, R _S = 10 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	3.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

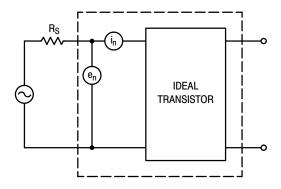
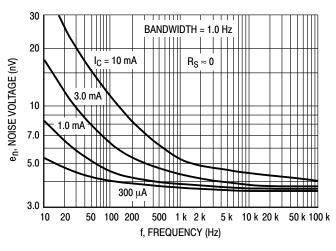


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

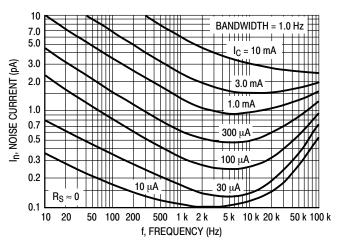
NOISE VOLTAGE



BANDWIDTH = 1.0 Hz 20 $R_S\approx 0\,$ en, NOISE VOLTAGE (nV) f = 10 Hz 10 100 Hz 7.0 1.0 kHz 5.0 3.0 0.02 0.01 0.05 0.1 0.2 0.5 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



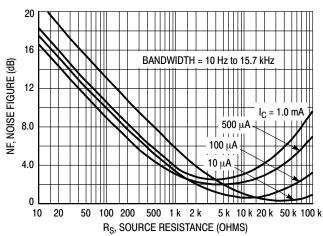
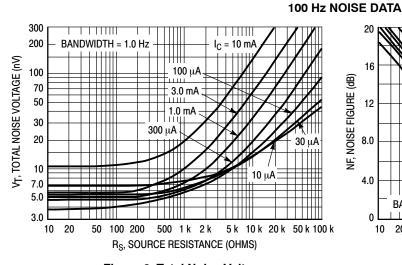


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



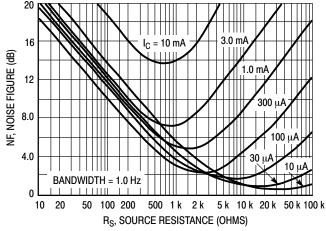


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

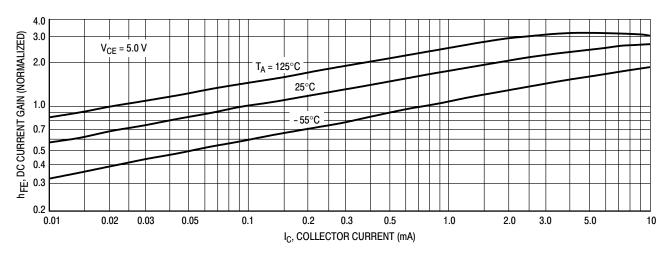


Figure 8. DC Current Gain

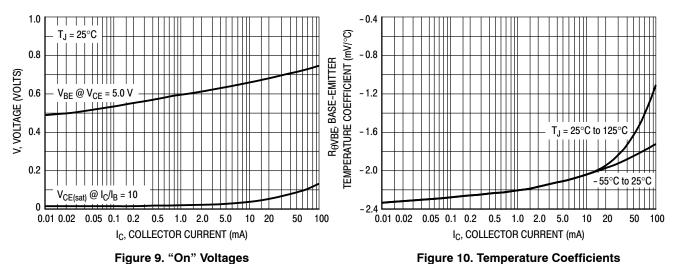


Figure 9. "On" Voltages

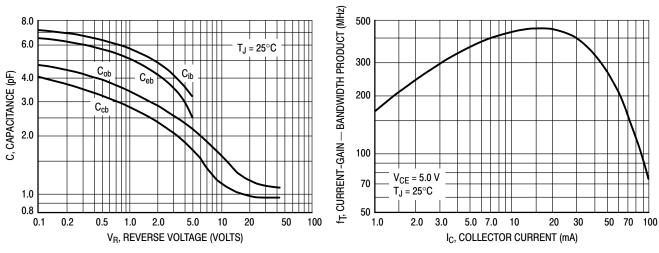


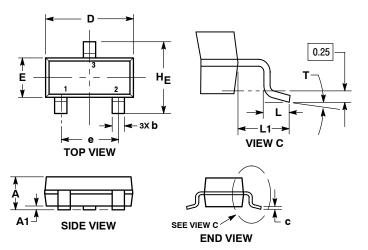
Figure 11. Capacitance

Figure 12. Current-Gain — Bandwidth Product

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08 ISSUE AR



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
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 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- I THE BASE MATERIAL.

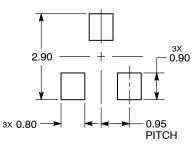
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10 °	0 °		10 °

STYLE 6:

- PIN 1. BASE
 - 2. EMITTER
 - 3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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